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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	Coldfire V1
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	CANbus, I²C, SCI, SPI, USB OTG
Peripherals	LVD, PWM, WDT
Number of I/O	66
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/pcf51jm128evlk

1 MCF51JM128 Family Configurations

1.1 Device Comparison

The MCF51JM128 series consists of the devices compared in Table 1.

Table 1. MCF51JM128 Series Device Comparison

Feature	MCF51JM128			MCF51JM64			MCF51JM32		
	80-pin	64-pin	44-pin	80-pin	64-pin	44-pin	80-pin	64-pin	44-pin
Flash memory size (KB)	128			64			32		
RAM size (KB)	16			16			16		
V1 ColdFire core with BDM (background debug module)	Yes								
ACMP (analog comparator)	Yes								
ADC channels (12-bit)	12		8	12		8	12		8
CAN (controller area network)	Yes	Yes	No	Yes	Yes	No	Yes	Yes	No
RNGA + CAU	Yes[1]								
CMT (carrier modulator timer)	Yes								
COP (computer operating properly)	Yes								
IIC1 (inter-integrated circuit)	Yes								
IIC2	Yes	No		Yes	No		Yes	No	
IRQ (interrupt request input)	Yes								
KBI (keyboard interrupts)	8	8	6	8	8	6	8	8	6
LVD (low-voltage detector)	Yes								
MCG (multipurpose clock generator)	Yes								
Port I/O[2]	66	51	33	66	51	33	66	51	33
RGPIO (rapid general-purpose I/O)	16	6	0	16	6	0	16	6	0
RTC (real-time counter)	Yes								
SCI1 (serial communications interface)	Yes								
SCI2	Yes								
SPI1 (serial peripheral interface)	Yes								
SPI2	Yes								
TPM1 (timer/pulse-width modulator) channels	6	6	4	6	6	4	6	6	4
TPM2 channels	2								
USBOTG (USB On-The-Go dual-role controller)	Yes								
XOSC (crystal oscillator)	Yes								

1 Only existed on special part number

1.3 Features

Table 2 describes the functional units of the MCF51JM128 series.

Table 2. MCF51JM128 Series Functional Units

Unit	Function
CF1CORE (V1 ColdFire core)	Executes programs and interrupt handlers
BDM (background debug module)	Provides a single-pin debugging interface (part of the V1 ColdFire core)
DBG (debug)	Provides debugging and emulation capabilities (part of the V1 ColdFire core)
SYSCTL (system control)	Provides LVD, COP, external interrupt request, and so on
FLASH (flash memory)	Provides storage for program code and constants
RAM (random-access memory)	Provides storage for program code, constants, and variables
RGPIO (rapid general-purpose input/output)	Allows I/O port access at CPU clock speeds
VREG (voltage regulator)	Controls power management throughout the device
USBOTG (USB On-The-Go)	Supports the USB On-The-Go dual-role controller
ADC (analog-to-digital converter)	Measures analog voltages at up to 12 bits of resolution
TPM1, TPM2 (timer/pulse-width modulators)	Provide a variety of timing-based features
CF1_INTC (interrupt controller)	Controls and prioritizes all device interrupts
CAU (cryptographic acceleration unit)	Co-processor support for DES, 3DES, AES, MD5, and SHA-1
RNGA (random number generator accelerator)	32-bit random number generator that complies with FIPS-140
RTC (real-time counter)	Provides a constant-time base with optional interrupt
ACMP (analog comparator)	Compares two analog inputs
CMT (carrier modulator timer)	Infrared output used for the Remote Controller
IIC1, IIC2 (inter-integrated circuits)	Supports the standard IIC communications protocol
KBI (keyboard interrupt)	Provides pin interrupt capabilities
MCG (multipurpose clock generator)	Provides clocking options for the device, including a phase-locked loop (PLL) and frequency-locked loop (FLL) for multiplying slower reference clock sources
XOSC (crystal oscillator)	Supports low/high range crystals
CAN (controller area network)	Supports standard CAN communications protocol
SCI1, SCI2 (serial communications interfaces)	Serial communications UARTs that can support RS-232 and LIN protocols
SPI1, SPI2 (serial peripheral interfaces)	Provide a 4-pin synchronous serial interface

Figure 3 shows the pinout of the 64-pin LQFP and QFP.

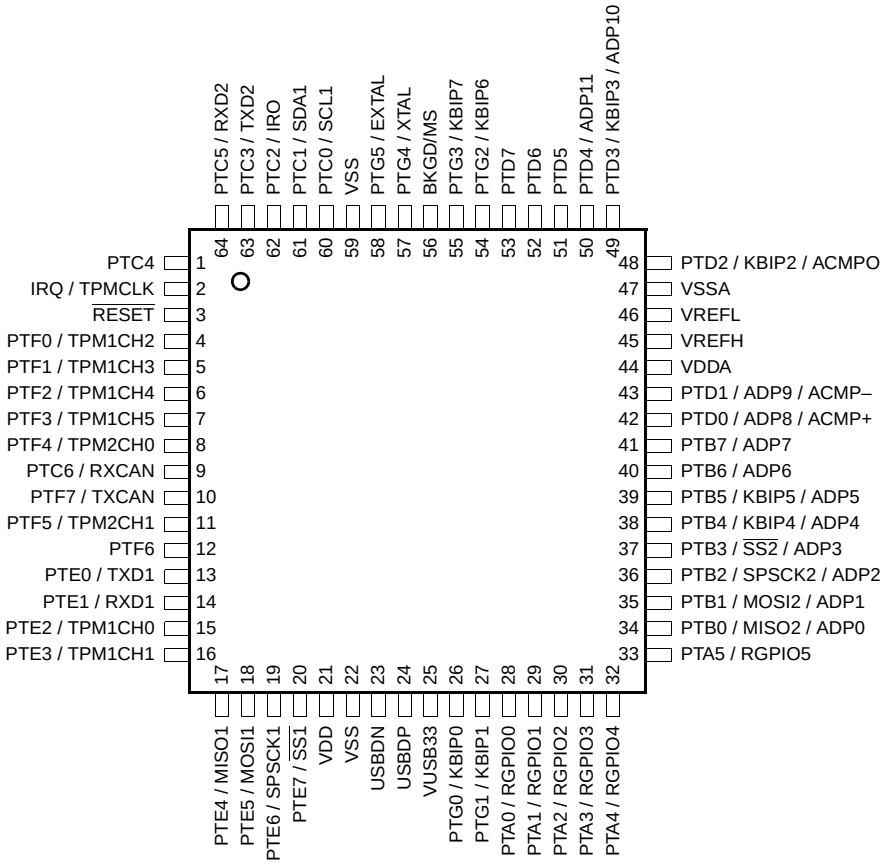


Figure 3. 64-pin QFP and LQFP

2 Preliminary Electrical Characteristics

This section contains electrical specification tables and reference timing diagrams for the MCF51JM128 microcontroller, including detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications.

The electrical specifications are preliminary and are from previous designs or design simulations. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle. These specifications will, however, be met for production silicon. Finalized specifications will be published after complete characterization and device qualifications have been completed.

NOTE

The parameters specified in this data sheet supersede any values found in the module specifications.

2.1 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 5. Parameter Classifications

P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled C in the parameter tables where appropriate.

2.2 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 6 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, V_{SS} or V_{DD}).

Table 10. DC Characteristics (continued)

Num	C	Parameter	Symbol	Min	Typ[1]	Max	Unit
7	P	Input low voltage; all digital inputs V_{DD} = 5V V_{DD} = 3V	V_{IL}	—	—	 1.75 1.05	V
8	P	Input hysteresis; all digital inputs	V_{hys}	0.06 x V_{DD}			mV
9	P	Input leakage current; input only pins[3]	$\|I_{In}\|$	—	0.1	1	µA
10	P	High Impedance (off-state) leakage current[3]	$\|I_{OZ}\|$	—	0.1	1	µA
11	P	Internal pullup resistors[4]	R_{PU}	20	45	65	kΩ
12	P	Internal pulldown resistors[5]	R_{PD}	20	45	65	kΩ
13		Internal pullup resistor to USBDP (to V_{USB33}) Idle Transmit	R_{PUPD}	 900 1425	 1300 2400	 1575 3090	kΩ
14	C	Input Capacitance; all non-supply pins	C_{In}	—	—	8	pF
15	D	RAM retention voltage[6]	V_{RAM}	—	0.6	1.0	V
16	P	POR rearm voltage	V_{POR}	0.9	1.4	2.0	V
17	D	POR rearm time	t_{POR}	10	—	—	µs
18	P	Low-voltage detection threshold — high range V_{DD} falling V_{DD} rising	V_{LVD1}	 3.9 4.0	 4.0 4.1	 4.1 4.2	V
19	P	Low-voltage detection threshold — low range V_{DD} falling V_{DD} rising	V_{LVD0}	 2.48 2.54	 2.56 2.62	 2.64 2.70	V
20	C	Low-voltage warning threshold — high range 1 V_{DD} falling V_{DD} rising	V_{LVW3}	 4.5 4.6	 4.6 4.7	 4.7 4.8	V
21	P	Low-voltage warning threshold — high range 0 V_{DD} falling V_{DD} rising	V_{LVW2}	 4.2 4.3	 4.3 4.4	 4.4 4.5	V
22	P	Low-voltage warning threshold low range 1 V_{DD} falling V_{DD} rising	V_{LVW1}	 2.84 2.90	 2.92 2.98	 3.00 3.06	V
23	C	Low-voltage warning threshold — low range 0 V_{DD} falling V_{DD} rising	V_{LVW0}	 2.66 2.72	 2.74 2.80	 2.82 2.88	V
24	T	Low-voltage inhibit reset/recover hysteresis 5 V 3 V	V_{hys}	 — —	 100 60	 — —	mV

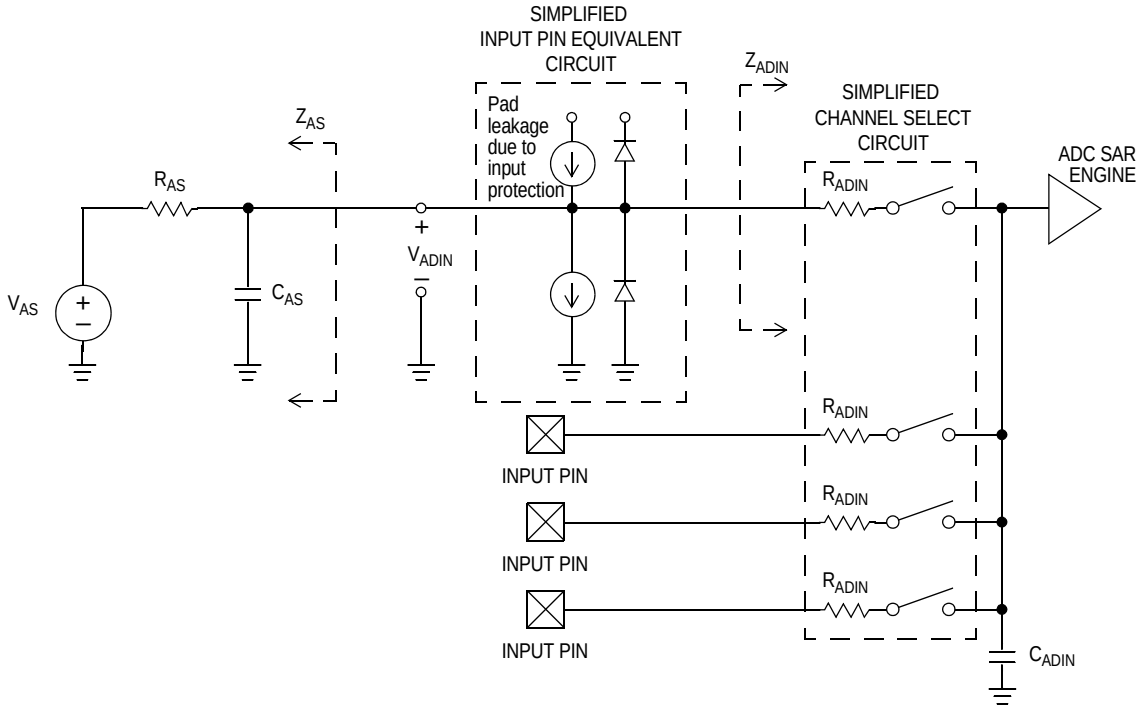


Figure 9. ADC Input Impedance Equivalency Diagram

Table 14. 5 Volt 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA})

Characteristic	Conditions	C	Symb	Min	Typ[1]	Max	Unit	Comment
Supply Current ADLPC=1 ADLSMP=1 ADCO=1		T	I_{DDAD}	—	133	—	µA	
Supply Current ADLPC=1 ADLSMP=0 ADCO=1		T	I_{DDAD}	—	218	—	µA	
Supply Current ADLPC=0 ADLSMP=1 ADCO=1		T	I_{DDAD}	—	327	—	µA	
Supply Current ADLPC=0 ADLSMP=0 ADCO=1		P	I_{DDAD}	—	0.582	1	mA	
Supply Current	Stop, Reset, Module Off		I_{DDAD}	—	0.011	1	µA	
ADC Asynchronous Clock Source	High Speed (ADLPC=0)	T	f_{ADACK}	2	3.3	5	MHz	t_{ADACK} = $1/f_{ADACK}$
	Low Power (ADLPC=1)			1.25	2	3.3		

2.9 External Oscillator (XOSC) Characteristics

Table 15. Oscillator Electrical Specifications (Temperature Range = –40 to 105°C Ambient)

Num	C	Rating	Symbol	Min	Typ[1]	Max	Unit
1		Oscillator crystal or resonator (EREFS = 1, ERCLKEN = 1) • Low range (RANGE = 0) • High range (RANGE = 1) FEE or FBE mode [2] • High range (RANGE = 1) PEE or PBE mode [3] • High range (RANGE = 1, HGO = 1) BLPE mode • High range (RANGE = 1, HGO = 0) BLPE mode	 f_{lo} $f_{hi\text{-}fll}$ $f_{hi\text{-}pll}$ $f_{hi\text{-}hgo}$ $f_{hi\text{-}lp}$	 32 1 1 1 1	 — — — — —	 38.4 5 16 16 8	 kHz MHz MHz MHz MHz
2		Load capacitors	C_1 C_2	See crystal or resonator manufacturer's recommendation.			
3		Feedback resistor • Low range (32 kHz to 38.4 kHz) • High range (1 MHz to 16 MHz)	R_F		10 1		MΩ MΩ
4	—	Series resistor • Low range, low gain (RANGE = 0, HGO = 0) • Low range, high gain (RANGE = 0, HGO = 1) ≥ 8 MHz 4 MHz 1 MHz • High range, low gain (RANGE = 1, HGO = 0) • High range, high gain (RANGE = 1, HGO = 1) ≥ 8 MHz 4 MHz 1 MHz	R_S	 — — — — — —	 0 100 0 0 0 0	 — — — 0 10 20	kΩ
5	T	Crystal start-up time [4] • Low range, low gain (RANGE = 0, HGO = 0) • Low range, high gain (RANGE = 0, HGO = 1) • High range, low gain (RANGE = 1, HG0 = 0)[5] • High range, high gain (RANGE = 1, HG0 = 1)[5]	 $t_{CSTL\text{-}LP}$ $t_{CSTL\text{-}HGO}$ $t_{CSTH\text{-}LP}$ $t_{CSTH\text{-}HGO}$	 — — — —	 200 400 5 15	 — — — —	ms
6	T	Square wave input clock frequency (EREFS = 0, ERCLKEN = 1) • FEE or FBE mode [2] • PEE or PBE mode [3] • BLPE mode	f_{extal}	0.03125 1 0	— — —	5 16 40	MHz MHz MHz

1 Data in Typical column was characterized at 5.0 V, 25°C or is typical recommended value.

2 When MCG is configured for FEE or FBE mode, input clock source must be divisible using RDIV to within the range of 31.25 kHz to 39.0625 kHz.

3 When MCG is configured for PEE or PBE mode, input clock source must be divisible using RDIV to within the range of 1 MHz to 2 MHz.

4 This parameter is characterized and not tested on each device. Proper PC board-layout procedures must be followed to achieve specifications.

5 4 MHz crystal

2.10 MCG Specifications

Table 16. MCG Frequency Specifications (Temperature Range = –40 to 125°C Ambient)

Num	C	Rating		Symbol	Min	Typical[1]	Max	Unit
1	P	Internal reference frequency - factory trimmed at V_{DD} = 5 V and temperature = 25 °C		f_{int_ft}	—	32.768	—	kHz
2	P	Average internal reference frequency – untrimmed		f_{int_ut}	31.25	—	39.0625	kHz
3	T	Internal reference startup time		t_{irefst}	—	60	100	µs
4	P	DCO output frequency range - untrimmed [2]	Low range (DRS=00)	f_{dco_ut}	16	—	20	MHz
	P		Mid range (DRS=01)		32	—	40	
	P		High range (DRS=10)		48	—	60	
5	P	DCO output frequency[2] Reference =32768Hz and DMX32 = 1	Low range (DRS=00)	f_{dco_DMX32}	—	19.92	—	MHz
	P		Mid range (DRS=01)		—	39.85	—	
	P		High range (DRS=10)		—	59.77	—	
6	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (using FTRIM)		$\Delta f_{dco\_res\_t}$	—	±0.1	±0.2	$\%f_{dco}$
7	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (not using FTRIM)		$\Delta f_{dco\_res\_t}$	—	±0.2	±0.4	$\%f_{dco}$
8	D	Total deviation of trimmed DCO output frequency over voltage and temperature		Δf_{dco_t}	—	0.5 –1.0	±2	$\%f_{dco}$
9	D	Total deviation of trimmed DCO output frequency over fixed voltage and temperature range of 0 – 70 °C		Δf_{dco_t}	—	±0.5	±1	$\%f_{dco}$
10	D	FLL acquisition time [3]		$t_{fll\_acquire}$	—	—	1	ms
11	D	PLL acquisition time [4]		$t_{pll\_acquire}$	—	—	1	ms
12	D	Long term Jitter of DCO output clock (averaged over 2ms interval) [5]		C_{Jitter}	—	0.02	0.2	$\%f_{dco}$
13	D	VCO operating frequency		f_{vco}	7.0	—	55.0	MHz
14	D	Jitter of PLL output clock measured over 625 ns[6]		$f_{pll\_jitter\_625ns}$	—	0.566[5]	—	$\%f_{pll}$
15	D	Lock entry frequency tolerance [7]		D_{lock}	±1.49	—	±2.98	%
16	D	Lock exit frequency tolerance [8]		D_{unl}	±4.47	—	±5.97	%
17	D	Lock time — FLL		t_{fll_lock}	—	—	$t_{fll\_acquire}$+ 1075(1/f_{int_t})	s
18	D	Lock time — PLL		t_{pll_lock}	—	—	$t_{pll\_acquire}$+ 1075(1/f_{pll_ref})	s
19	D	Loss of external clock minimum frequency – RANGE = 0		f_{loc_low}	(3/5) x f_{int}	—	—	kHz

1 Data in Typical column was characterized at 5.0 V, 25C or is typical recommended value

2 The resulting bus clock frequency should not exceed the maximum specified bus clock frequency of the device.

3 This specification applies to any time the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

4 This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

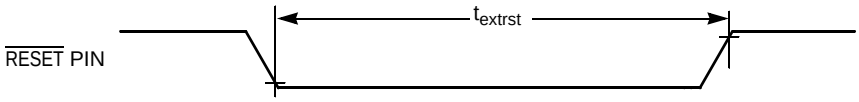


Figure 10. Reset Timing

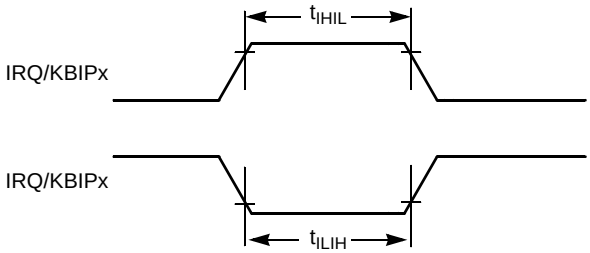


Figure 11. IRQ/KBIPx Timing

2.11.2 Timer/PWM (TPM) Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 18. TPM Input Timing

NUM	C	Function	Symbol	Min	Max	Unit
1	—	External clock frequency	f_{TPMext}	dc	$f_{Bus}/4$	MHz
2	—	External clock period	t_{TPMext}	4	—	t_{cyc}
3	D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
4	D	External clock low time	t_{clkl}	1.5	—	t_{cyc}
5	D	Input capture pulse width	t_{ICPW}	1.5	—	t_{cyc}

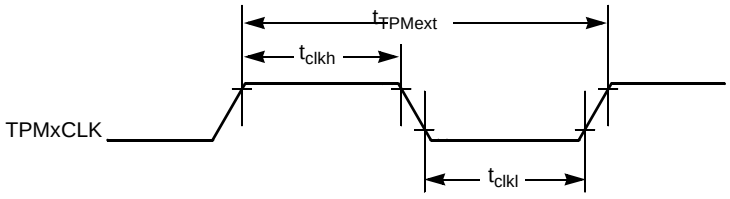
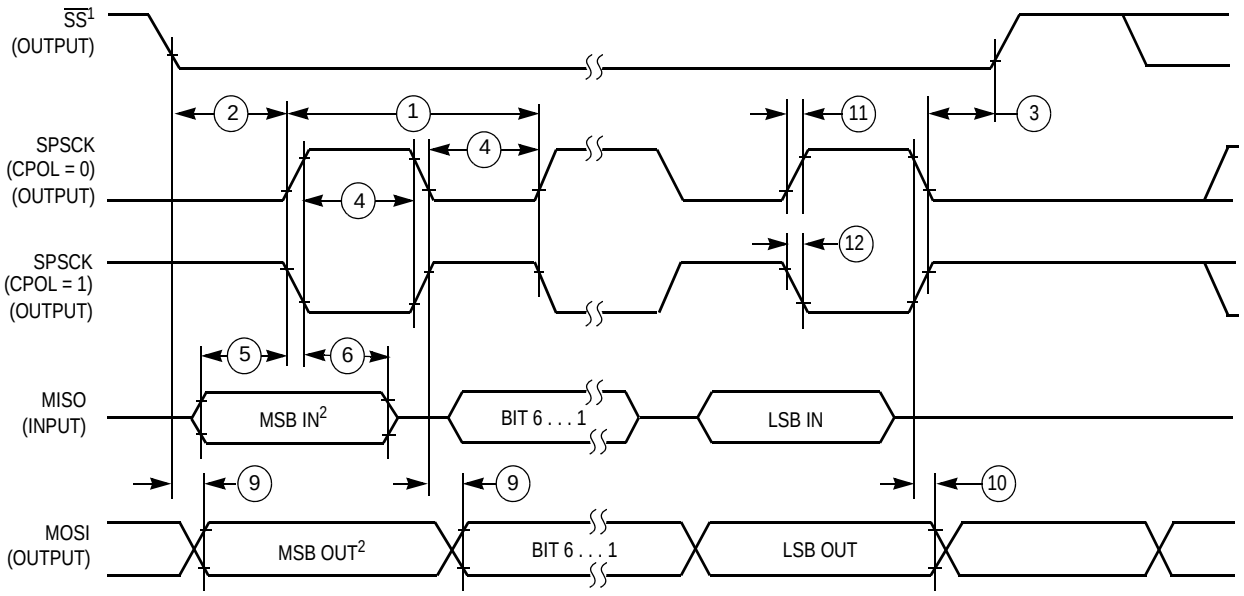


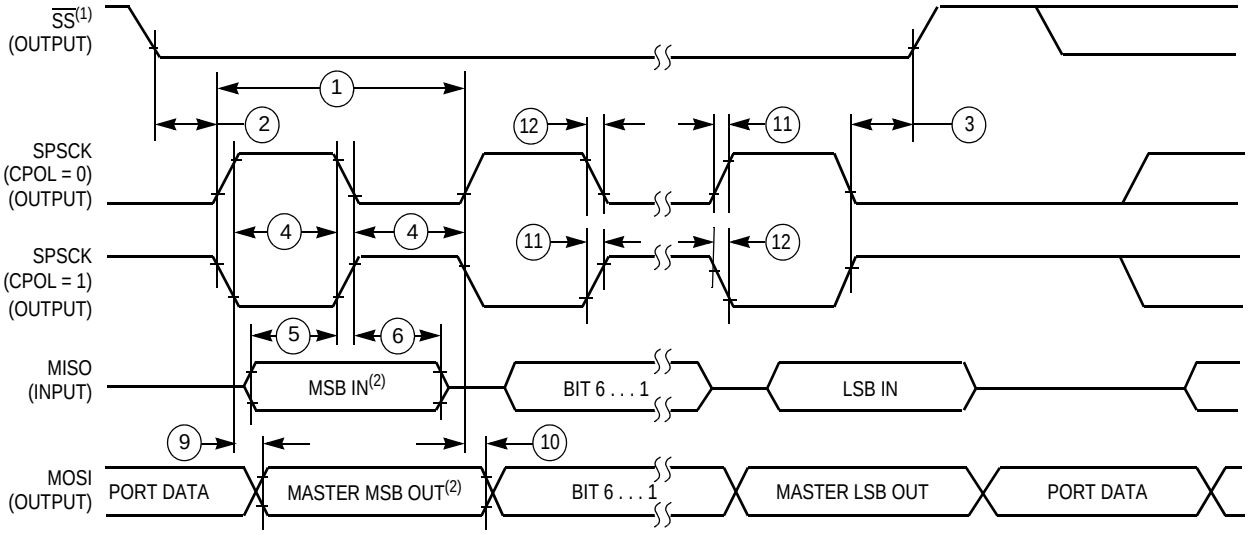
Figure 12. Timer External Clock



NOTES:

1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 14. SPI Master Timing (CPHA = 0)



NOTES:

1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 15. SPI Master Timing (CPHA = 1)

2.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the Flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply.

Table 21. Flash Characteristics

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
1		Supply voltage for program/erase	$V_{prog/erase}$	2.7		5.5	V
2		Supply voltage for read operation	V_{Read}	2.7		5.5	V
3		Internal FCLK frequency[2]	f_{FCLK}	150		200	kHz
4		Internal FCLK period (1/FCLK)	t_{Fcyc}	5		6.67	µs
5		Byte program time (random location)(2)	t_{prog}	9			t_{Fcyc}
6		Byte program time (burst mode)(2)	t_{Burst}	4			t_{Fcyc}
7		Page erase time[3]	t_{Page}	4000			t_{Fcyc}
8		Mass erase time(2)	t_{Mass}	20,000			t_{Fcyc}
9	C	Program/erase endurance[4] T_L to T_H = –40°C to + 105°C T = 25°C		10,000 —	— 100,000	— —	cycles
10		Data retention[5]	t_{D_ret}	15	100	—	years

1 Typical values are based on characterization data at V_{DD} = 5.0 V, 25°C unless otherwise stated.

2 The frequency of this clock is controlled by a software setting.

3 These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

4 Typical endurance for Flash was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale Semiconductor defines typical endurance, please refer to Engineering Bulletin EB619/D, *Typical Endurance for Nonvolatile Memory*.

5 Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale Semiconductor defines typical data retention, please refer to Engineering Bulletin EB618/D, Typical Data Retention for Nonvolatile Memory.

2.14 USB Electricals

The USB electricals for the USBOTG module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit http://www.usb.org.

If the Freescale USBOTG implementation requires additional or deviant electrical characteristics, this space would be used to communicate that information.

Table 22. Internal USB 3.3V Voltage Regulator Characteristics

	Symbol	Unit	Min	Typ	Max
Regulator operating voltage	V_{regin}	V	3.9	—	5.5
Vreg output	V_{regout}	V	3	3.3	3.6
Vusb33 input with internal Vreg disabled	$V_{usb33in}$	V	3	3.3	3.6
VREG Quiescent Current	I_{VRQ}	mA	—	0.5	—

2.15 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

2.15.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM Cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (North and East). For more detailed information concerning the evaluation results, conditions and setup, please refer to the EMC Evaluation Report for this device.

3 Mechanical Outline Drawings

3.1 80-pin LQFP

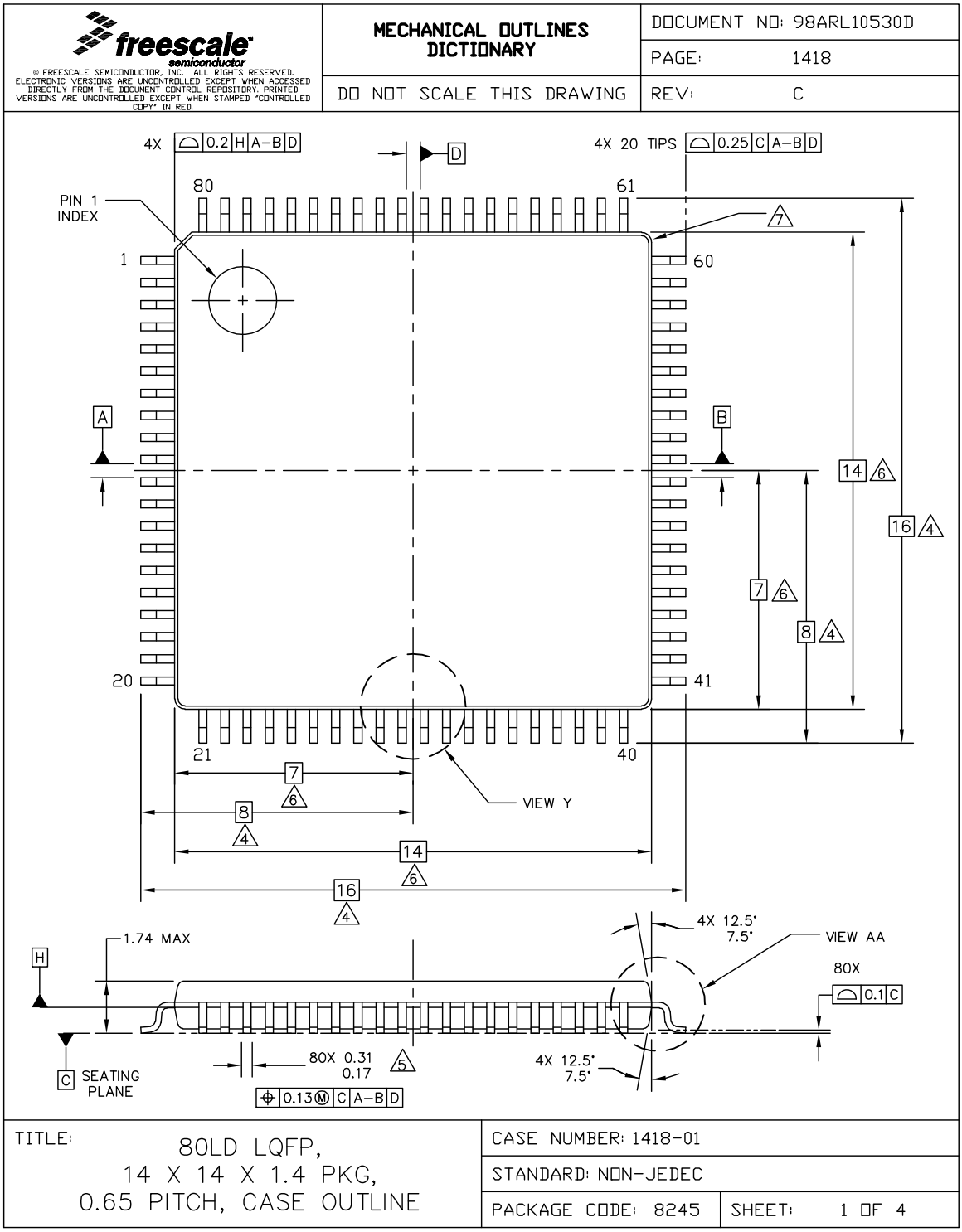


Figure 18. 80-pin LQFP Diagram - I

3.2 64-pin LQFP

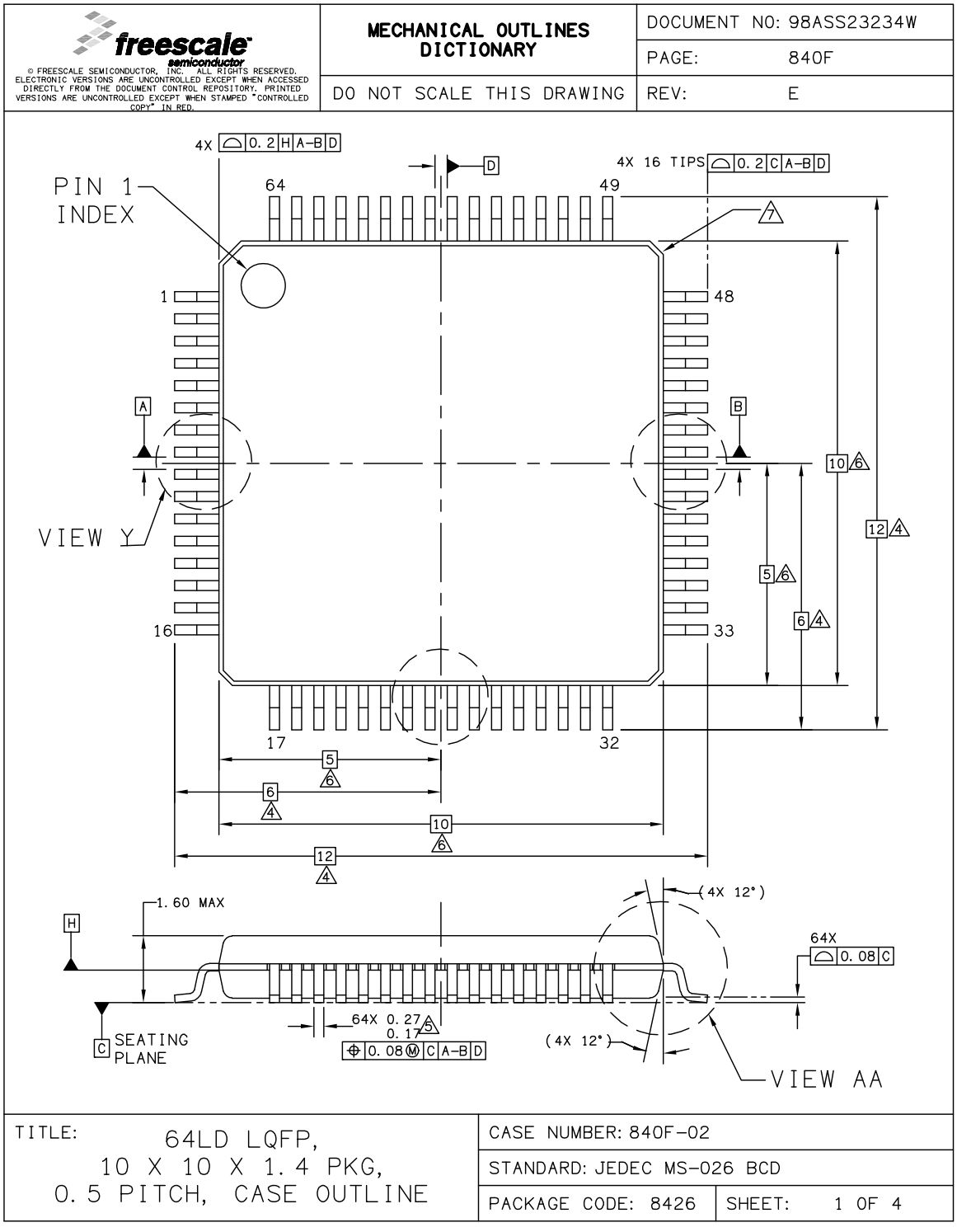


Figure 21. 64-pin LQFP Diagram - I

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		PAGE: 840F
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NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994.
3. DATUMS A, B AND D TO BE DETERMINED AT DATUM PLANE H.
4. DIMENSIONS TO BE DETERMINED AT SEATING PLANE C.
5. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE UPPER LIMIT BY MORE THAN 0.08 mm AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD SHALL NOT BE LESS THAN 0.07 mm.
6. THIS DIMENSION DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. THIS DIMENSION IS MAXIMUM PLASTIC BODY SIZE DIMENSION INCLUDING MOLD MISMATCH.
7. EXACT SHAPE OF EACH CORNER IS OPTIONAL.
8. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.1 mm AND 0.25 mm FROM THE LEAD TIP.

TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	CASE NUMBER: 840F–02	
	STANDARD: JEDEC MS–026 BCD	
	PACKAGE CODE: 8426	SHEET: 3

Figure 23. 64-pin LQFP Diagram - III

3.3 64-pin QFP

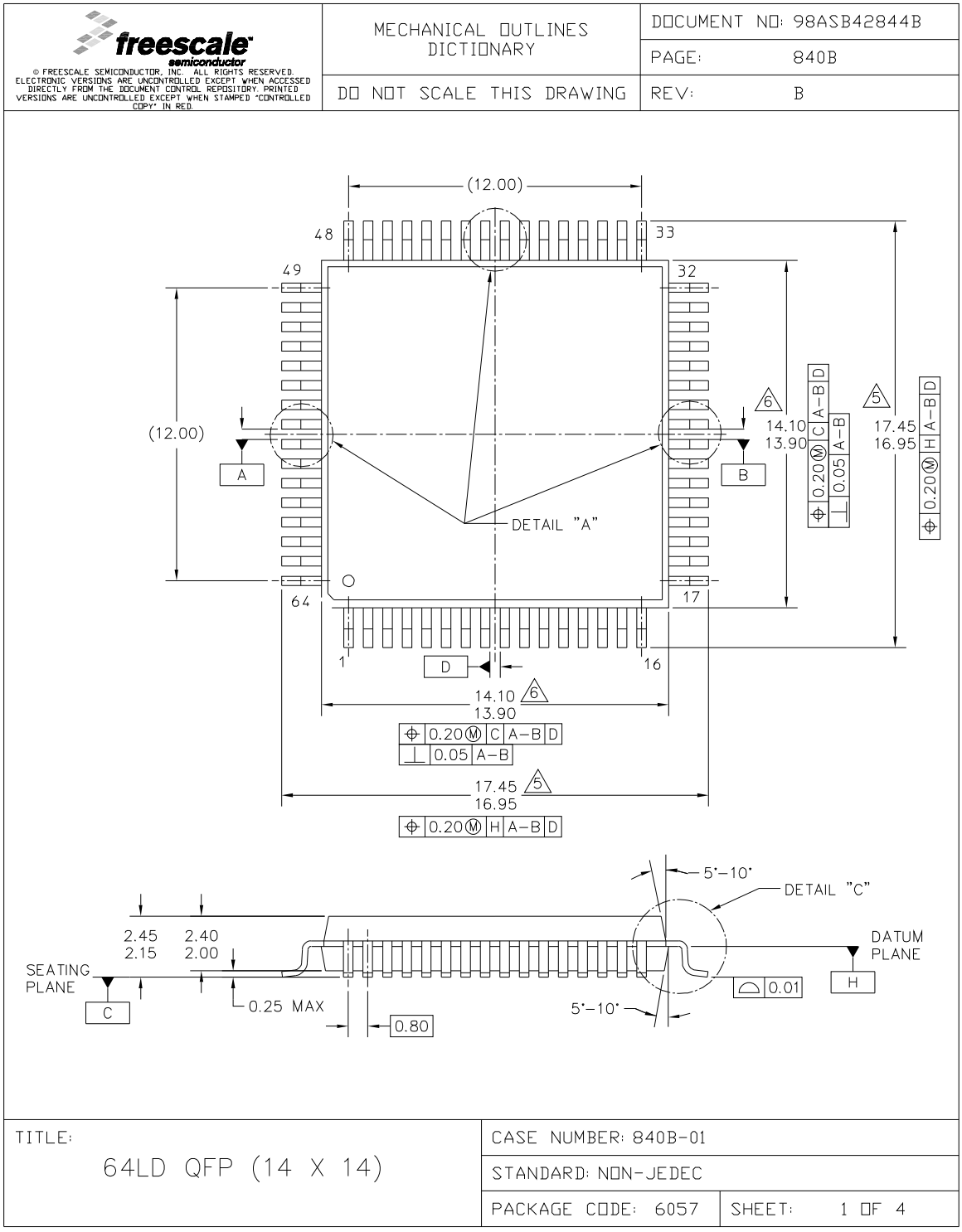

Figure 24. 64-pin QFP Diagram - I

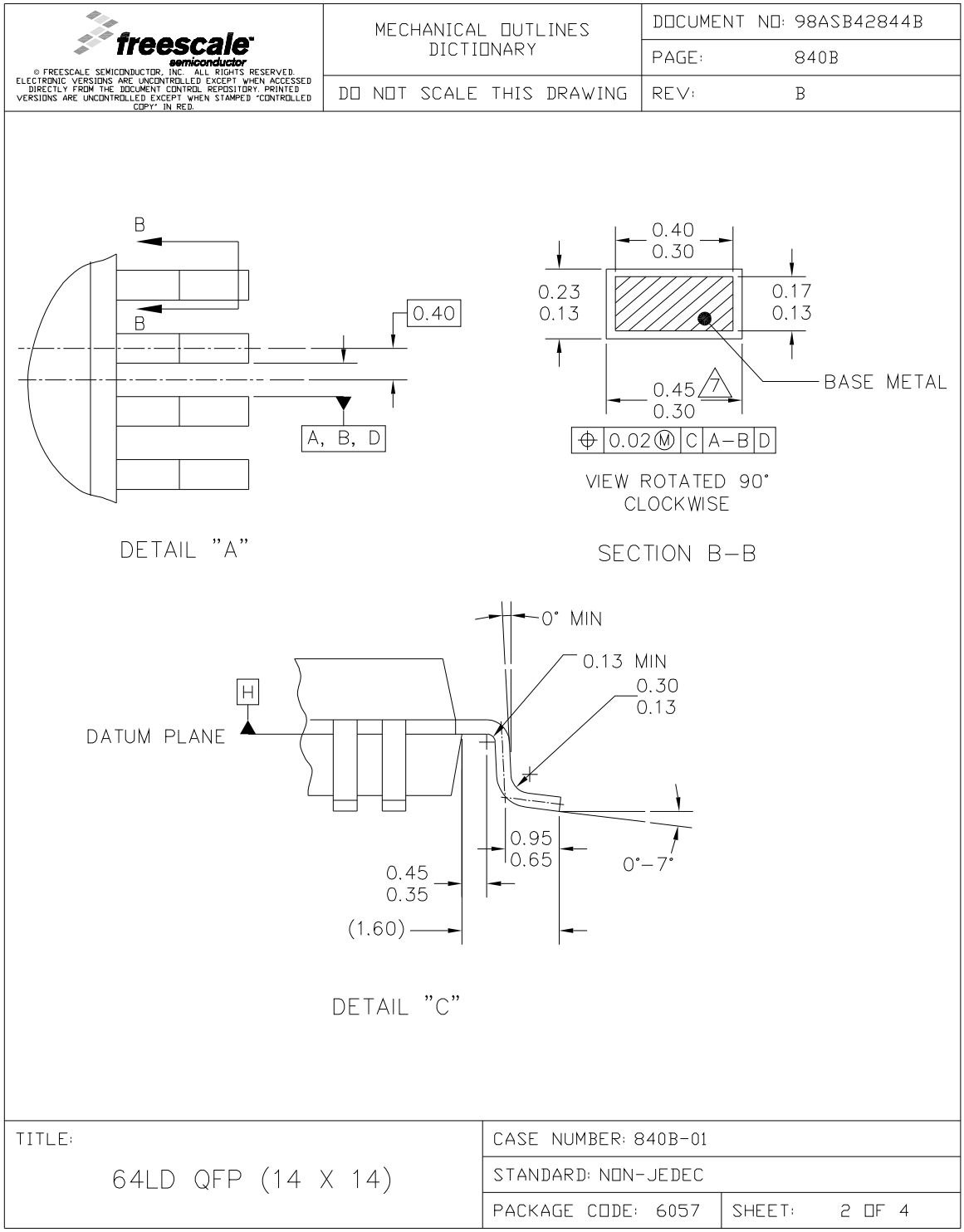

Figure 25. 64-pin QFP Diagram - II

3.4 44-pin LQFP

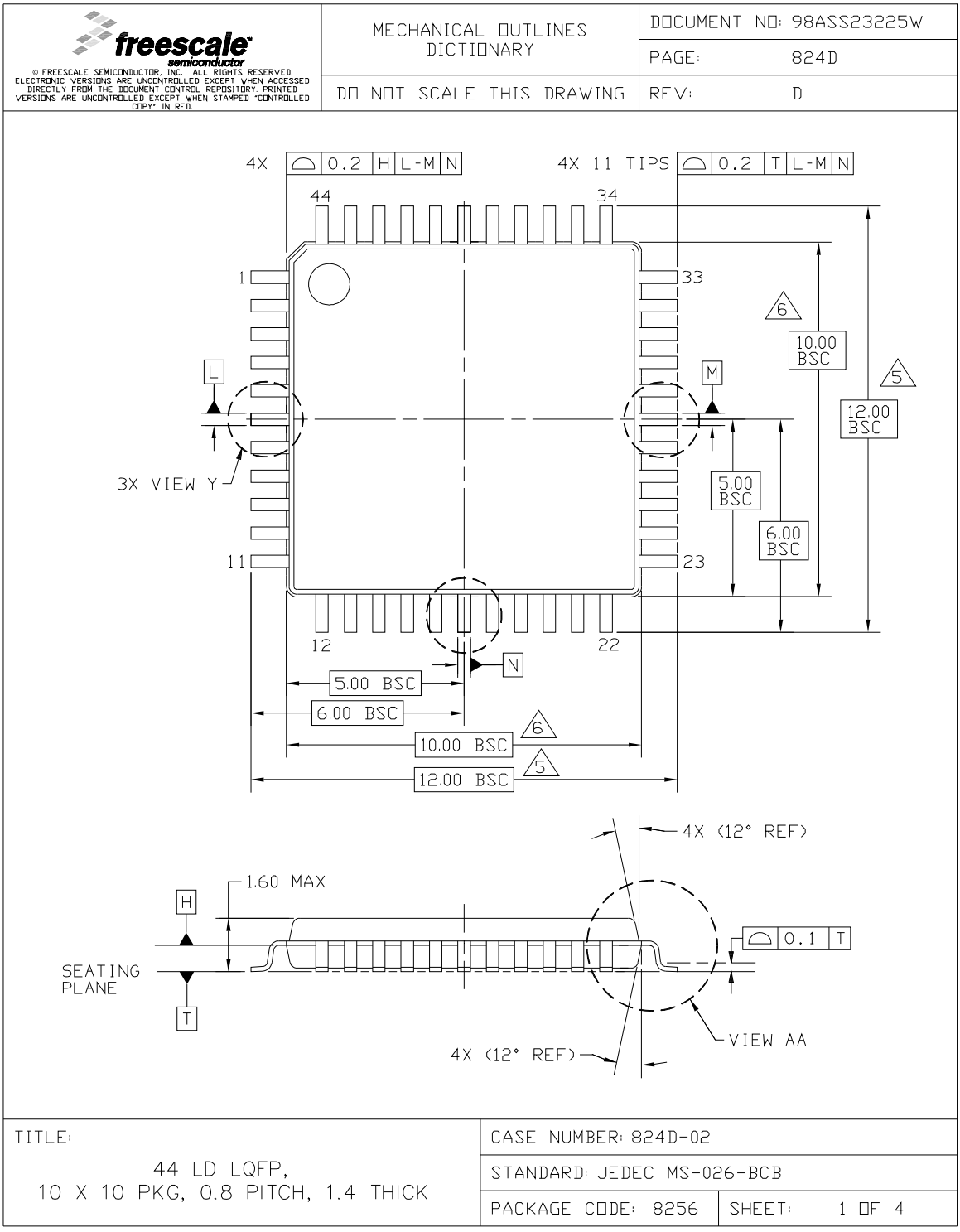

Figure 27. 44-pin LQFP Diagram - I

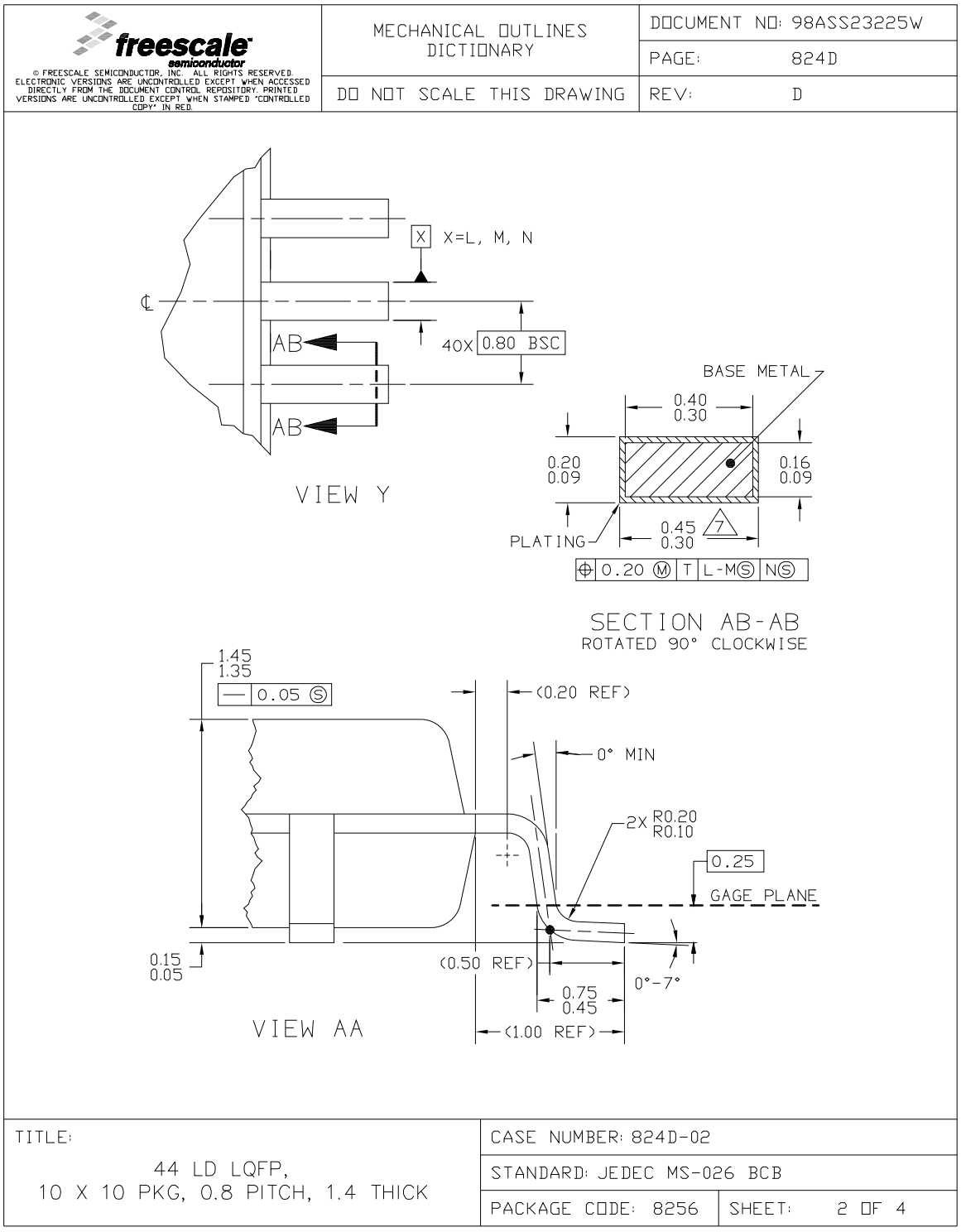

Figure 28. 44-pin LQFP Diagram - II

4 Revision History

This section lists major changes between versions of the MCF51JM128 Data Sheet document.

Table 23. Changes Between Revisions

Revision	Description
1	Updated features list Updated the figures Typical Low-side Drive (sink) characteristics – High Drive (PTxDSn = 1), Typical Low-side Drive (sink) characteristics – Low Drive (PTxDSn = 0), and Typical High-side Drive (source) characteristics – High Drive (PTxDSn = 1) Added the figure Typical High-side Drive (source) characteristics – Low Drive (PTxDSn = 0) Updated the table Supply Current Characteristics Updated the table Oscillator Electrical Specifications (Temperature Range = –40 to 105×C Ambient) Updated the table SPI Electrical Characteristic, DC Characteristics
2	Updated the table Orderable Part Number Summary, DC Characteristics, and Supply Current Characteristics
3	Updated the table Orderable Part Number Summary, MCG Characteristics, SPI Characteristics, and Supply Current Characteristics Changed V_{DDAD} to V_{DDA}, V_{SSAD} to V_{SSA} Updated the table Device comparison
4	Added “RAM retention voltage” parameter in “DC Characteristics” table, alongwith a table note. Added “Temp sensor voltage” parameter in “5 Volt 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA})” table. Added “ “Temp sensor slope” parameter in 5 Volt 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) table. Also, corrected unit of “Temp sensor voltage” parameter in 5 Volt 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) table.